

Power Transistor (50V, 3A)

2SD1760 / 2SD1864

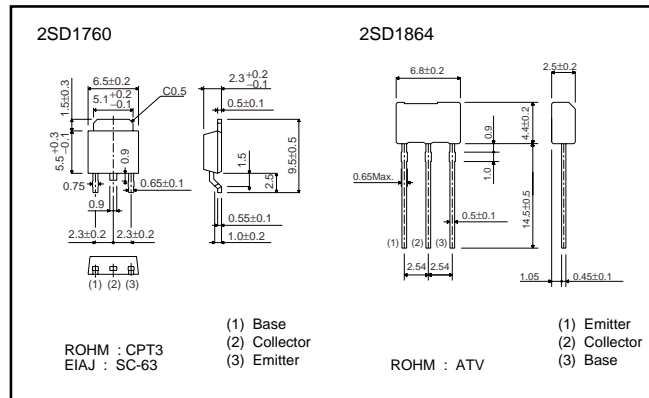
●Features

- Low $V_{CE(sat)}$.
 $V_{CE(sat)} = 0.5V$ (Typ.)
 $(I_c/I_b = 2A / 0.2A)$
- Complements the 2SB1184 / 2SB1243.

●Structure

Epitaxial planar type
 NPN silicon transistor

●External dimensions (Units : mm)



●Absolute maximum ratings ($T_a=25^\circ C$)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_c	3	A (DC)
		4.5	A (Pulse) ^{*1}
Collector power dissipation	2SD1760	15	W ($T_c=25^\circ C$) ^{*2}
	2SD1864	1	W
Junction temperature	T_j	150	$^\circ C$
Storage temperature	T_{stg}	-55~+150	$^\circ C$

^{*1} Single pulse, $P_w=100ms$

^{*2} Printed circuit board, 1.7mm thick, collector copper plating 100mm² or larger.

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●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	60	-	-	V	I _c =50μA
Collector-emitter breakdown voltage	BV _{CE0}	50	-	-	V	I _c =1mA
Emitter-base breakdown voltage	BV _{EB0}	5	-	-	V	I _E =50μA
Collector cutoff current	I _{CB0}	-	-	1	μA	V _{CB} =40V
Emitter cutoff current	I _{EB0}	-	-	1	μA	V _{EB} =4V
Collector-emitter saturation voltage	V _{CE(sat)}	-	0.5	1	V	I _c /I _b =2A/0.2A
DC current transfer ratio	h _{FE}	82	-	390	-	V _{CE} =3V, I _c =0.5A
Transition frequency	f _T	-	90	-	MHZ	V _{CE} =5V, I _E =500mA, f=30MHZ
Output capacitance	C _{ob}	-	40	-	pF	V _{CB} =10V, I _E =0A, f=1MHZ

* Measured using pulse current.

●Packaging specifications and h_{FE}

Type	h _{FE}	Package	Taping	
		Code	TL	TV2
		Basic ordering unit (pieces)	2500	2500
2SD1760	PQR		○	-
2SD1864	PQR		-	○

h_{FE} values are classified as follows:

Item	P	Q	R
h _{FE}	82~180	120~270	180~390

●Electrical characteristic curves

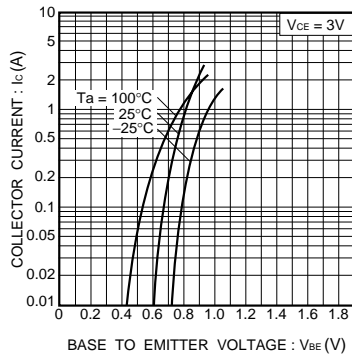


Fig.1 Grounded emitter propagation characteristics

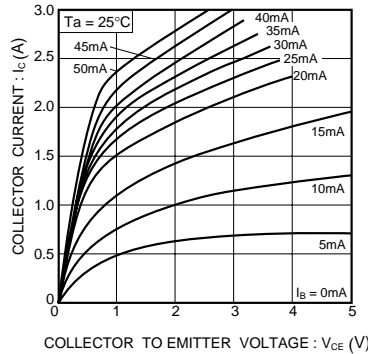


Fig.2 Grounded emitter output characteristics (I)

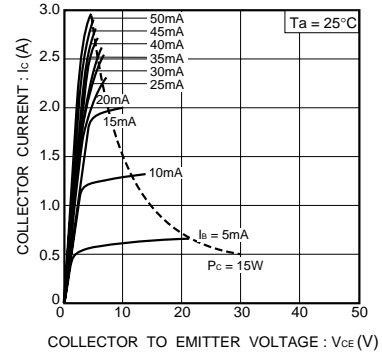


Fig.3 Grounded-emitter output characteristics(II)

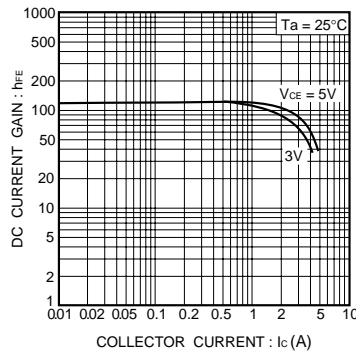


Fig.4 DC current gain vs. collector current(I)

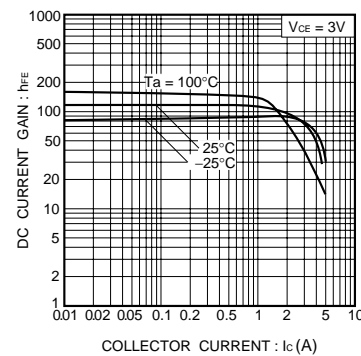


Fig.5 DC current gain vs. collector current(II)

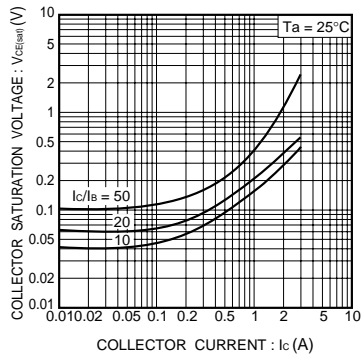


Fig.6 Collector-emitter saturation voltage vs. collector current



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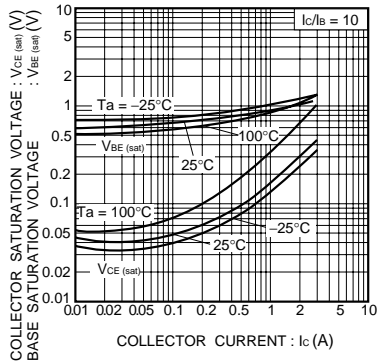


Fig.7 Collector-emitter saturation voltage vs. collector current
Base-emitter saturation voltage vs. collector current

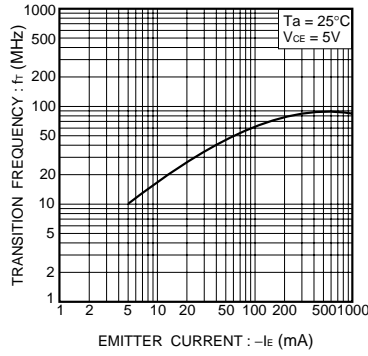


Fig.8 Gain bandwidth product vs. emitter current

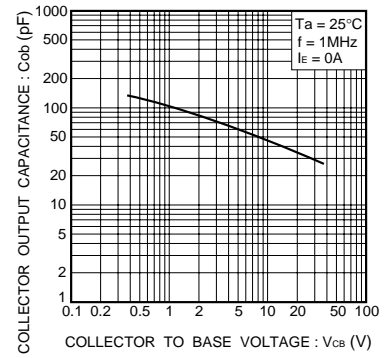


Fig.9 Collector output capacitance vs. collector-base voltage

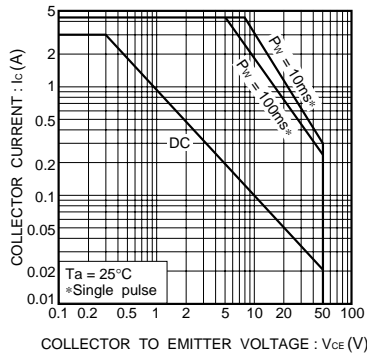


Fig.10 Safe operating area (2SD1760)

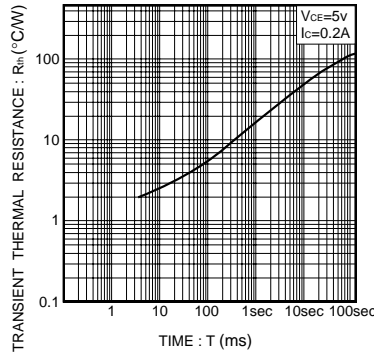


Fig.11 Transient thermal resistance (2SD1760)

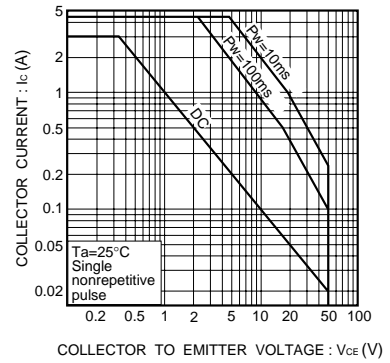


Fig.12 Safe operating area (2SD1864)

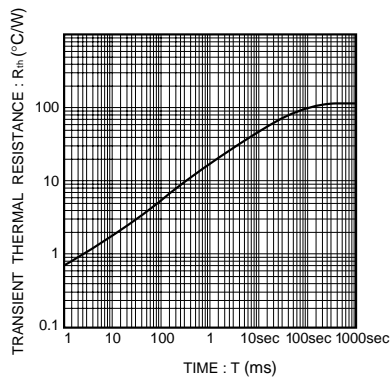


Fig.13 Transient thermal resistance (2SD1864)

单击下面可查看定价，库存，交付和生命周期等信息

[>>ROHM Semiconductor \(罗姆\)](#)